

Title (en)

METHOD FOR THE PRODUCTION OF A BIPOLAR TRANSISTOR COMPRISING AN IMPROVED BASE TERMINAL

Title (de)

VERFAHREN ZUR HERSTELLUNG EINES BIPOLARTRANSISTORS MIT VERBESSERTER BASISANSCHLUSS

Title (fr)

PROCEDE DE PRODUCTION D'UN TRANSISTOR BIPOLAIRE DOTE D'UNE BORNE DE BASE AMELIOREE

Publication

EP 1726038 A1 20061129 (DE)

Application

EP 05706930 A 20050119

Priority

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- DE 102004013478 A 20040318

Abstract (en)

[origin: WO2005098926A1] The invention relates to the production of an improved bipolar transistor provided with a low-ohmic base terminal. According to said method, a dielectric layer is to be deposited on a semi-conductor substrate and high doping is to be carried via an implantation mask. In a subsequent controlled thermal step, the dopant is then diffused inside the semi-conductor substrate by the dielectric layer which acts as a dopant store. As a result, a low-ohmic region is produced which defines the extrinsic base in a precise manner.

IPC 8 full level

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CPC (source: EP US)

H01L 29/66242 (2013.01 - EP US); **H01L 29/66287** (2013.01 - EP US)

Citation (search report)

See references of WO 2005098926A1

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